# 2SC5244, 2SC5244A

### Silicon NPN triple diffusion mesa type

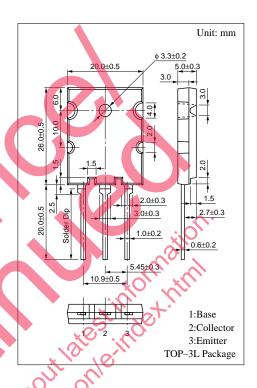
For horizontal deflection output

#### **Features**

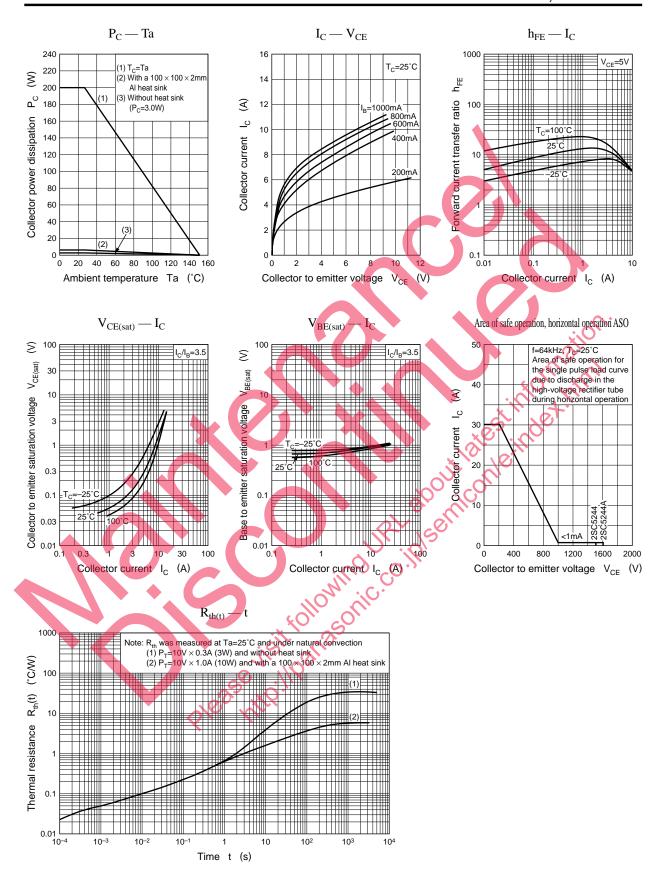
- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide area of safe operation (ASO)

### Absolute Maximum Ratings (T<sub>C</sub>=25°C)

Parameter		Symbol	Ratings	Unit		
Collector to	2SC5244	N/	1500	V		
base voltage	2SC5244A	$V_{CBO}$	1600	V		
Collector to	2SC5244	V	1500	N.		
emitter voltage	2SC5244A	V <sub>CES</sub>	1600			
Emitter to base voltage		$V_{EBO}$	6	V		
Peak collector current		$I_{CP}$	20	A		
Collector current		$I_{\rm C}$	30	A		
Collector power	T <sub>C</sub> =25°C	D	200	W		
dissipation	Ta=25°C	$P_{C}$	3.5	W		
Junction temperature		$T_j$	150	°C		
Storage temperature		$T_{stg}$	-55 to +150	<i>Q</i> -3°.		



emitter voltage 2SC5244A V <sub>CE</sub>	ES 16	00 V			1	Base Collector					
Emitter to base voltage V <sub>EB</sub>	30	V	Jel about late 2 in a service on the service of the		3:Emitter TOP–3L Package						
Peak collector current I <sub>CP</sub>	2	0 A	(10)	<u>S</u>	101-3L	1 ackage					
Collector current I <sub>C</sub>	30	0 A	, cO/								
Collector power T <sub>C</sub> =25°C	20	0 W	ilo								
dissipation Ta=25°C P <sub>C</sub>	3.	5 " 0 (0)									
Junction temperature T <sub>j</sub>	15	°C									
Storage temperature T <sub>stg</sub>	-55 to	+150 °C									
■ Electrical Characteristics (T <sub>C</sub> =25°C) + Collaboration											
Parameter	Symbol	Conditions	min	typ	max	Unit					
Collector cutoff 2SC5244		$V_{CB} = 1500V, I_E = 0$			1	mA					
current 2SC5244A	$I_{CBO}$	$V_{\rm CB} = 1600  \text{V},  I_{\rm E} = 0$			1	IIIA					
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 5V, I_C = 0$			50	μΑ					
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 5V, I_{C} = 10A$	5		12						
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 10A, I_B = 2.8A$			3	V					
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 10A, I_B = 2.8A$			1.5	V					
Transition frequency	$f_T$	$V_{CE} = 10V, I_{C} = 0.1A, f = 0.5MHz$		3		MHz					
Storage time	t <sub>stg</sub>	$I_C = 12A$ , $I_{B1} = 2.4A$ , $I_{B2} = -4.8A$ ,		1.5	2.5	μs					
Fall time	t <sub>f</sub>	Resistance loaded		0.12	0.2	μs					



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